

#### **Description**

The NVMFS5C468NT1G uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

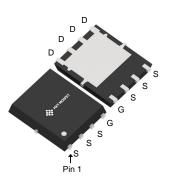
 $V_{DS} = 40V$   $I_D = 40A$   $R_{DS(ON)} < 14m\Omega$   $V_{GS} = 10V$ 

### **Application**

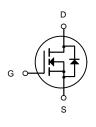
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

**Package Marking and Ordering Information** 

Pr	oduct ID	Pack	Brand	Qty(PCS)	
N۷	/MFS5C468NT1G	DFN5X6-8L	HXY MOSFET	5000	

#### Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	40	V
Vgs	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	40	А
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, Vos @ 10V1	28	Α
Ідм	Pulsed Drain Current <sup>2</sup>	160	Α
EAS	Single Pulse Avalanche Energy <sup>3</sup>	50	mJ
Тэтс	Storage Temperature Range	-55 to 175	°C
TJ	Operating Junction Temperature Range	-55 to 175	°C



#### N-Channel Enhancement Mode MOSFET

## Electrical Characteristics (T<sub>C</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit		
Off Characteristics								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	-	-	V		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA		
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA		
On Characteristics (Note 3)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.6	2.5	V		
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	11	14	mΩ		
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	30	-	-	S		
Dynamic Characteristics (Note4)	·		•	,				
Input Capacitance	C <sub>lss</sub>	)/ 05)/)/ 0)/	-	1540	-	PF		
Output Capacitance	Coss	$V_{DS}$ =25 $V$ , $V_{GS}$ =0 $V$ , F=1.0MHz	-	171	-	PF		
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVITIZ	-	115	-	PF		
Switching Characteristics (Note 4)								
Turn-on Delay Time	t <sub>d(on)</sub>		-	5.0	-	nS		
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =20V, $I_D$ =20A, $R_{\overline{c}}$ =1 $\Omega$	-	24	-	nS		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{GEN}$ =3 $\Omega$	-	38	-	nS		
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS		
Total Gate Charge	Qg	V 00VI 00A	-	24	-	nC		
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =30V,I <sub>D</sub> =30A, V <sub>GS</sub> =10V	-	5.9	-	nC		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	3.6	-	nC		
Drain-Source Diode Characteristics								
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =30A	-	-	1.2	V		
Diode Forward Current (Note 2)	Is		-	-	48	Α		
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =30A	-	9		nS		
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	15		nC		
Forward Turn-On Time	d Turn-On Time ton Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)							

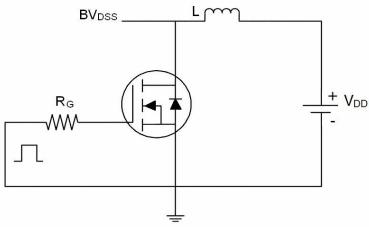
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition: Tj=25  $^{\circ}$ C,V<sub>DD</sub>=30V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$

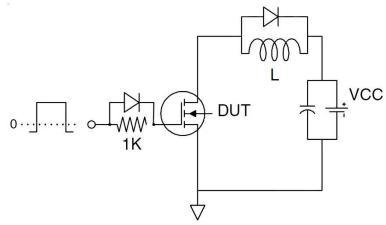


### **Test circuit**

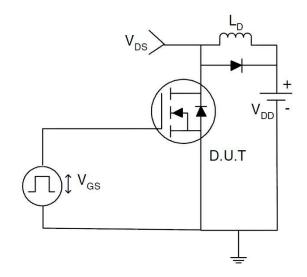
## 1) E<sub>AS</sub> test Circuits



### 2) Gate charge test Circuit

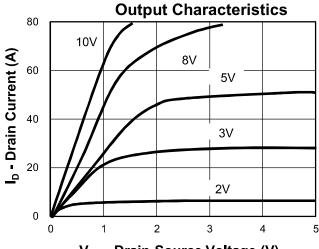


### 3) Switch Time Test Circuit

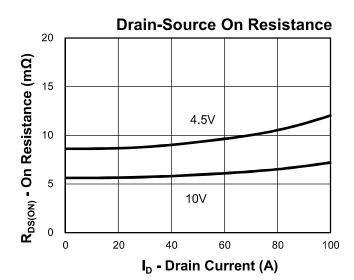


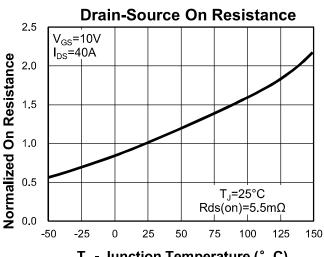


### **Typical Performance Characteristics**

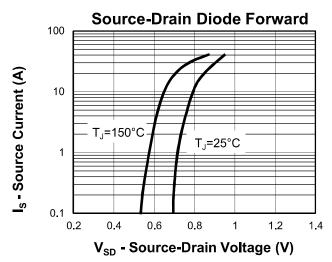




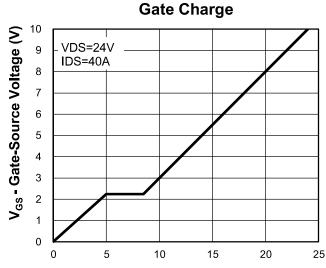




T<sub>.1</sub> - Junction Temperature (° C)

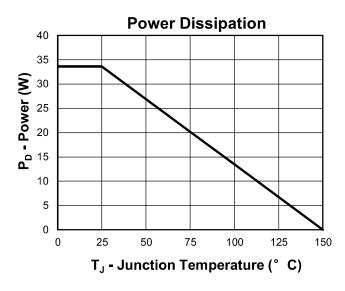


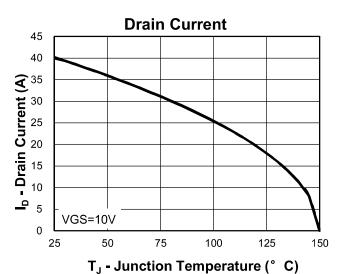


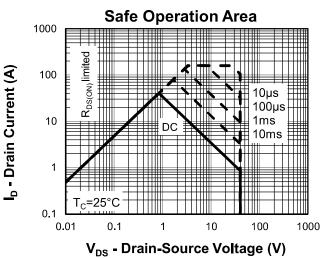


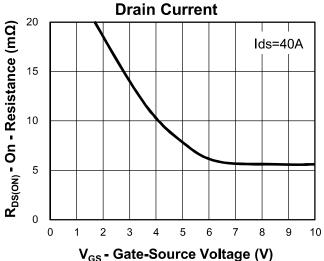
Q<sub>G</sub> - Gate Charge (nC)



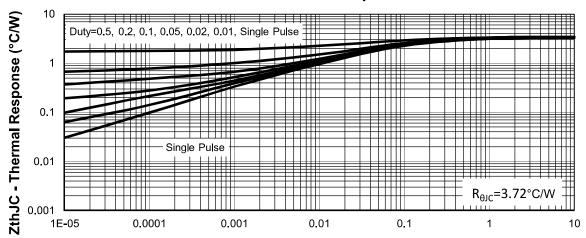






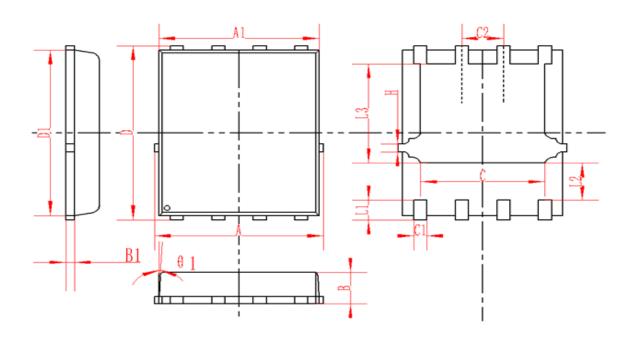






**Square Wave Pulse Duration (sec)** 

# **DFN5X6-8L Package Information**



SYMBOL	MM		INCH			
STIVIDOL	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1		0.254REF			0.010REF	
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	C2 1.27TYP		0.5TYP			
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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